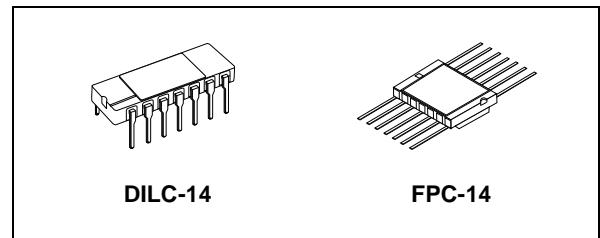


## RAD HARD HEX INVERTER (SINGLE STATE)

- HIGH SPEED:  
 $t_{PD} = 5\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 10\%$   $V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OHL}| = I_{OL} = 4\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH  
54 SERIES 04
- SPACE GRADE-1: ESA SCC QUALIFIED
- 50 krad QUALIFIED, 100 krad AVAILABLE ON  
REQUEST
- NO SEL UNDER HIGH LET HEAVY IONS  
IRRADIATION
- DEVICE FULLY COMPLIANT WITH  
SCC-9401-055



**Table 1: Order Codes**

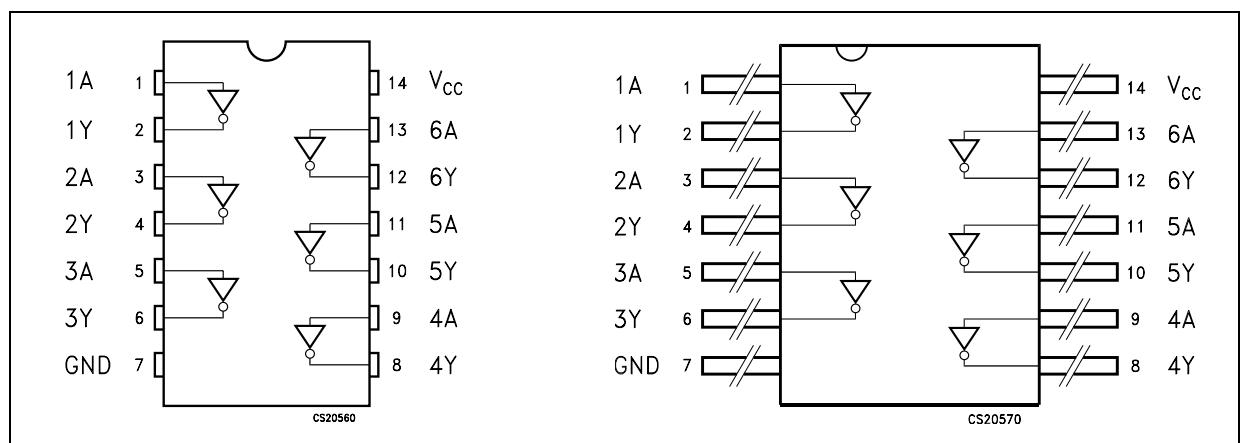
PACKAGE	FM	EM
DILC	M54HCU04D	M54HCU04D1
FPC	M54HCU04K	M54HCU04K1

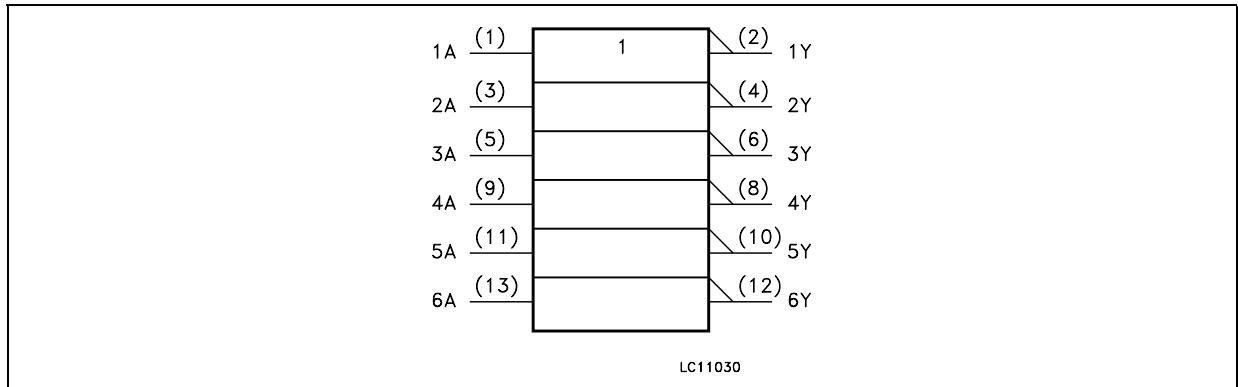
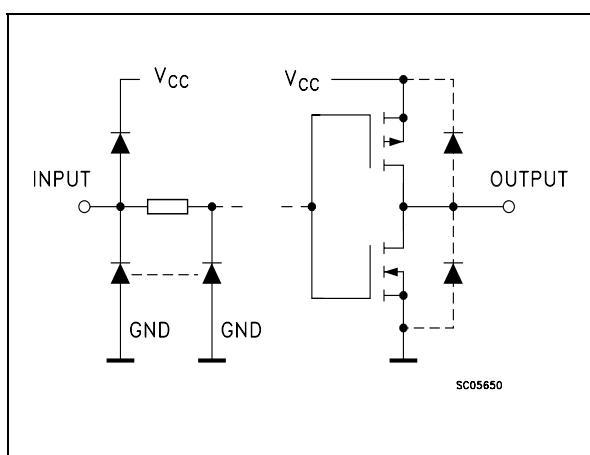
As internal circuit is composed of a single stage inverter, it can be used in crystal oscillator. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### DESCRIPTION

The M54HCU04 is an high speed CMOS HEX INVERTER (SINGLE STATE) fabricated with silicon gate C<sup>2</sup>MOS technology.

**Figure 1: Pin Connection**



**Figure 2: IEC Logic Symbols**

**Figure 3: Input And Output Equivalent Circuit**

**Table 2: Pin Description**

PIN N°	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

**Table 3: Truth Table**

A	Y
L	H
H	L

**Table 4: Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
P <sub>D</sub>	Power Dissipation	300	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**Table 5: Recommended Operating Conditions**

Symbol	Parameter	Value		Unit	
$V_{CC}$	Supply Voltage	2 to 6		V	
$V_I$	Input Voltage	0 to $V_{CC}$		V	
$V_O$	Output Voltage	0 to $V_{CC}$		V	
$T_{op}$	Operating Temperature	-55 to 125		°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000		ns
		$V_{CC} = 4.5V$	0 to 500		ns
		$V_{CC} = 6.0V$	0 to 400		ns

**Table 6: DC Specifications**

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$V_{IH}$	High Level Input Voltage	2.0		1.7			1.7		1.7		V
		4.5		3.6			3.6		3.6		
		6.0		4.8			4.8		4.8		
$V_{IL}$	Low Level Input Voltage	2.0			0.3		0.3		0.3		V
		4.5			0.9		0.9		0.9		
		6.0			1.2		1.2		1.2		
$V_{OH}$	High Level Output Voltage	2.0	$I_O = -20 \mu A$	1.8	2.0		1.8		1.8		V
		4.5	$I_O = -20 \mu A$	4.0	4.5		4.0		4.0		
		6.0	$I_O = -20 \mu A$	5.5	5.9		5.5		5.5		
		4.5	$I_O = -4.0 mA$	4.18	4.31		4.13		4.10		
		6.0	$I_O = -5.2 mA$	5.68	5.8		5.63		5.60		
$V_{OL}$	Low Level Output Voltage	2.0	$I_O = 20 \mu A$		0.0	0.2		0.2		0.2	V
		4.5	$I_O = 20 \mu A$		0.0	0.5		0.5		0.5	
		6.0	$I_O = 20 \mu A$		0.1	0.5		0.5		0.5	
		4.5	$I_O = 4.0 mA$		0.17	0.26		0.33		0.40	
		6.0	$I_O = 5.2 mA$		0.18	0.26		0.33		0.40	
$I_I$	Input Leakage Current	6.0	$V_I = V_{CC} \text{ or GND}$			$\pm 0.1$		$\pm 1$		$\pm 1$	$\mu A$
$I_{CC}$	Quiescent Supply Current	6.0	$V_I = V_{CC} \text{ or GND}$			1		10		20	$\mu A$

**Table 7: AC Electrical Characteristics ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6\text{ns}$ )**

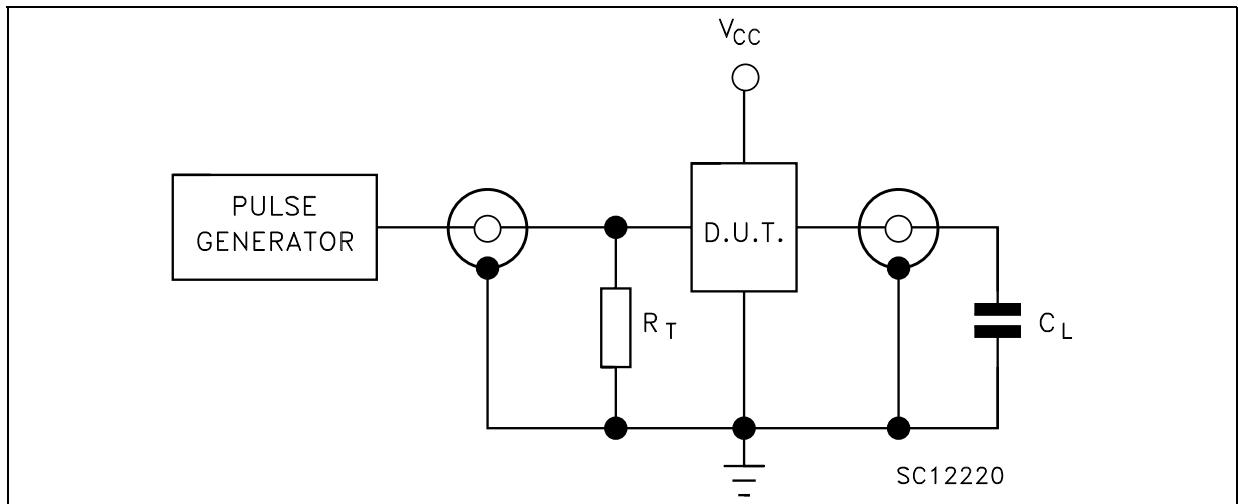
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$t_{TLH} t_{THL}$	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
$t_{PLH} t_{PHL}$	Propagation Delay Time	2.0			18	60		75		90	ns
		4.5			6	12		15		18	
		6.0			5	10		13		15	

Table 8: Capacitive Characteristics

Symbol	Parameter	Test Condition		Value						Unit		
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C			
				Min.	Typ.	Max.	Min.	Max.	Min.			
C <sub>IN</sub>	Input Capacitance	5.0				5	10		10		pF	
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0				13					pF	

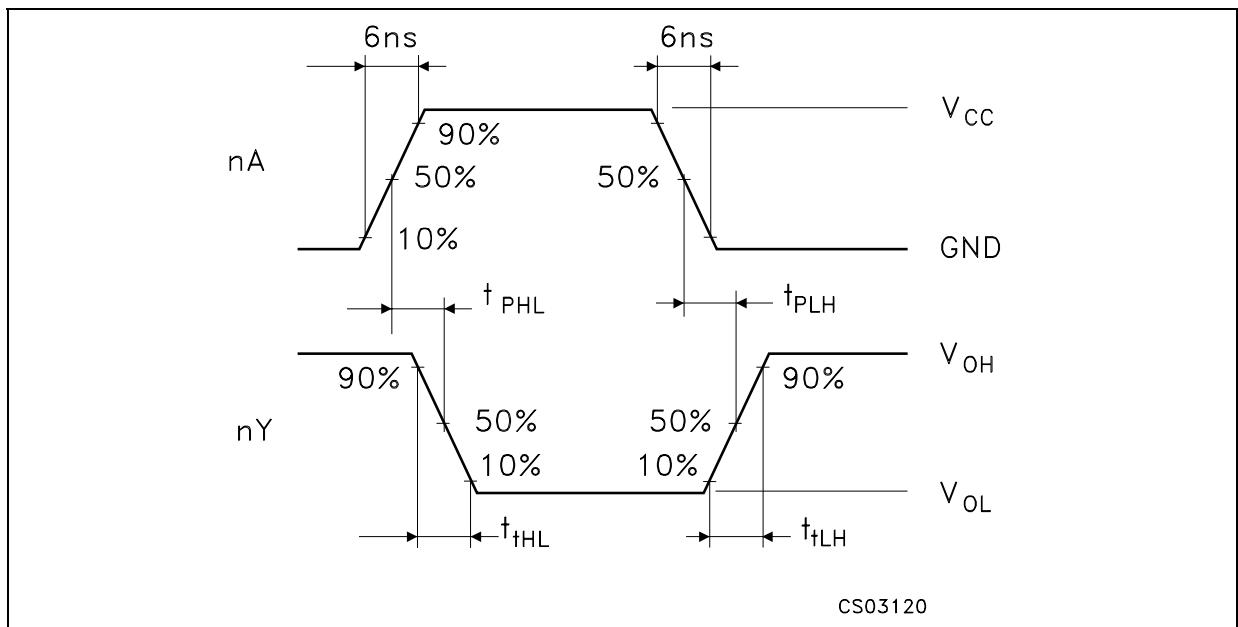
1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> × V<sub>CC</sub> × f<sub>IN</sub> + I<sub>CC</sub>

Figure 4: Test Circuit



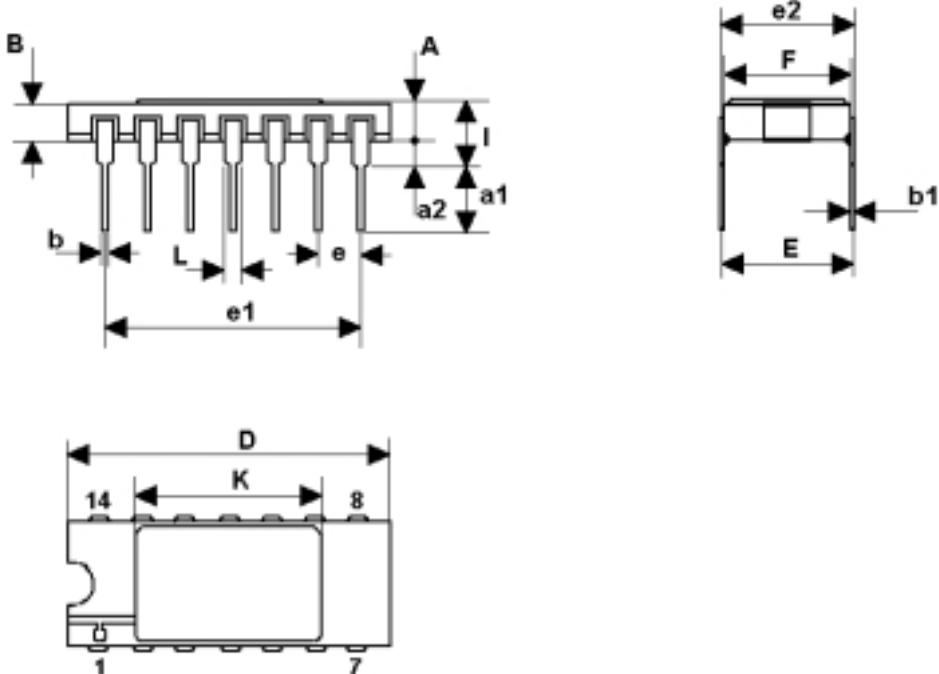
C<sub>L</sub> = 50pF or equivalent (includes jig and probe capacitance)  
R<sub>T</sub> = Z<sub>OUT</sub> of pulse generator (typically 50Ω)

Figure 5: Waveform - Propagation Delay Time (f=1MHz; 50% duty cycle)



## DILC-14 MECHANICAL DATA

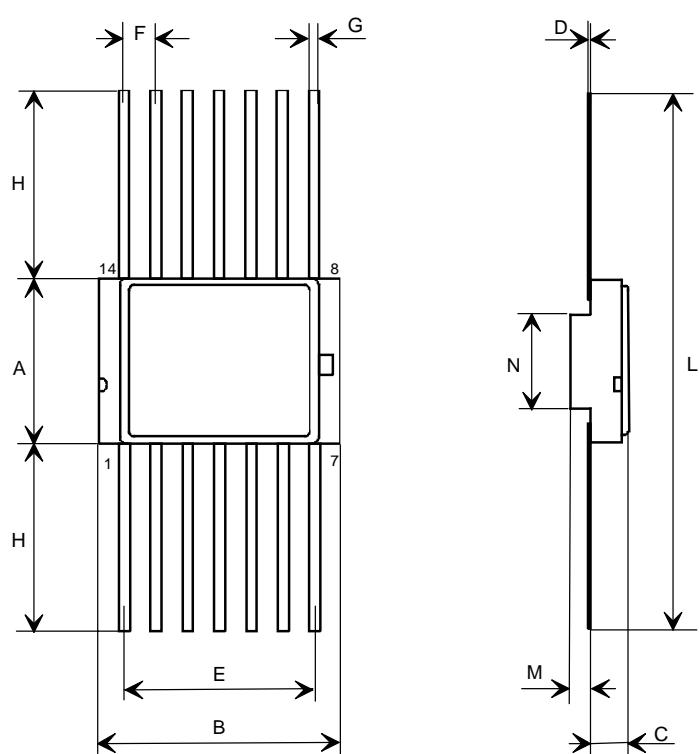
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		2.54	0.083		0.100
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.82	2.03	2.39	0.072	0.080	0.094
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	18.79	19.00	19.20	0.740	0.748	0.756
E	7.36	7.62	7.87	0.290	0.300	0.310
e		2.54			0.100	
e1	15.11	15.24	15.37	0.595	0.600	0.605
e2	7.62	7.87	8.12	0.300	0.310	0.320
F	7.11		7.75	0.280		0.305
I			3.70			0.146
K	10.90		12.1	0.429		0.476
L	1.14	1.27	1.5	0.045	0.050	0.059



0016173H

## FPC-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	6.75	6.91	7.06	0.266	0.272	0.278
B	9.76	9.95	10.14	0.384	0.392	0.399
C	1.49		1.95	0.059		0.077
D	0.10	0.127	0.15	0.004	0.005	0.006
E	7.50	7.62	7.75	0.295	0.300	0.305
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H		6.0			0.236	
L	18.75		22.0	0.738		0.866
M		0.38			0.015	
N		4.31			0.170	



016029E

**Table 9: Revision History**

Date	Revision	Description of Changes
27-Jun-2004	1	First Release

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